VUSB010R25ANA

Datasheet

General Description

$V_{(BR)DSS}$	$R_{DS(ON)\_max}$	I_D
100V	250mΩ@10V	2A
	260mΩ@6V	
	270mΩ@4.5V	

Symbol

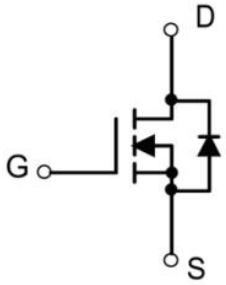


Figure 1 Symbol of VUSB010R25ANA

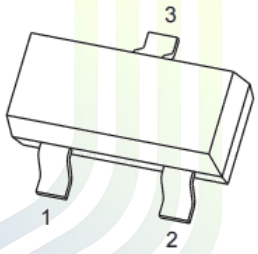
Features

- Trench FET Power MOSFET
- Exceptional on-resistance and maximum DC current capability

Application

- DC/DC Converter
- Load Switch for Portable Devices
- Battery Switch

Package Type



1. GATE
2. SOURCE
3. DRAIN

SOT-23

Figure 2 Package Type of VUSB010R25ANA

Ordering Information

Product Name	Package
VUSB010R25ANA	SOT-23

Absolute Maximum Ratings (T_A= 25 ºC, unless otherwise specified)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	100	V
Gate-Source Voltage	V_{GSS}	±20	V
Continuous Drain Current[Note1]	I_D	2	A
Total Power Dissipation[Note4]	P_D	0.35	W
Junction Temperature	T_J	150	ºC
Storage Temperature	T_{STG}	-55 to 150	ºC

Thermal Resistance

Parameter	Symbol	Min	Typ	Max	Unit
Thermal Resistance, Junction-to-Ambient[Note2]	$R_{\theta JA}$		357		ºC/W

Electrical Characteristics (T_A= 25 ºC, unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Statistic Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D= 250uA	100			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}= 80V, V_{GS}=0V			1	uA
Gate-Body Leakage Current	I_{GSS}	V_{GS} = ±20V, V_{DS}= 0V			±100	nA
Gate Threshold Voltage[Note3]	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250uA	1.2	1.5	2.5	V
Static Drain-Source On-Resistance[Note3]	$R_{DS(ON)}$	V_{GS}=10V, I_D= 1.5A		195	250	mΩ
		V_{GS}=6V, I_D= 1A		200	260	
		V_{GS}=4.5V, I_D= 0.5A		208	270	
Forward Transconductance[Note3]	g_{FS}	V_{DS}=20V, I_D= 1A	1			S
Dynamic Characteristics						
Input Capacitance	C_{ISS}	V_{DS}=50V		190		pF
Output Capacitance	C_{OSS}	V_{GS}=0V		22		pF
Reverse Transfer Capacitance	C_{RSS}	f=1MHz		13		pF
Total Gate Charge	Q_g	V_{DS}=50V		5.2		nC
Gate-Source Charge	Q_{gs}	V_{GS}=10V		0.75		
Gate-Drain Charge	Q_{gd}	I_D= 1.3A		1.4		
Switching Parameters						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}= 50V		6		ns
Turn-on Rise Time	t_r	V_{GS}= 10V		10		
Turn-off Delay Time	$t_{d(off)}$	I_D= 1.3A		10		
Turn-off Fall Time	t_f	R_G=1Ω, R_L=39Ω		6		
Diode Characteristics						
Diode Forward Voltage [Note3]	V_{SD}	V_{GS}=0V, I_S= 0.44A			1.0	V

Notes :

1. The maximum current rating is limited by package.And device mounted on a large heatsink.
2. Device mounted on 1in2 FR-4 board with 1oz. Copper, in a still air environment with T_A =25°C.
3. Pulse Test : Pulse Width ≤ 300μs, duty cycle ≤ 2%.
4. The power dissipation P_D is limited by $T_{J(MAX)}$ = 150°C.And device mounted on a large heatsink

Typical Performance Characteristics

Figure 3: Transfer Characteristics

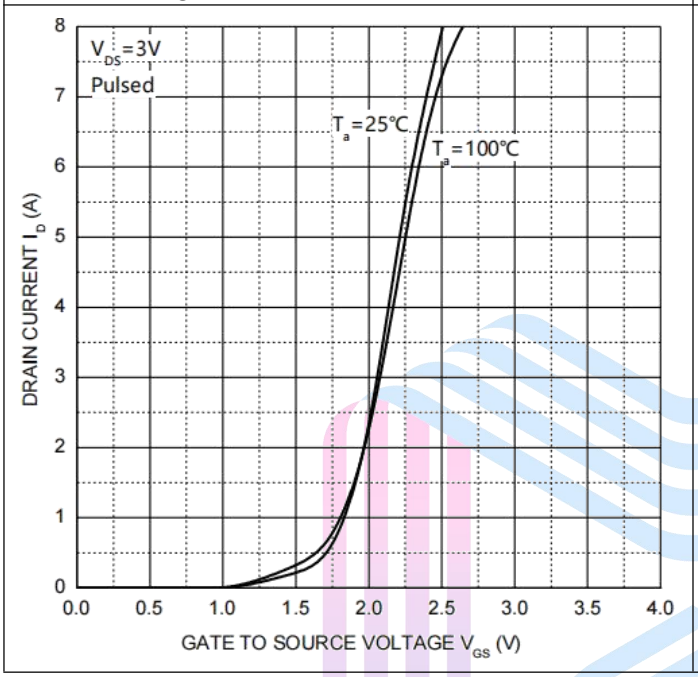


Figure 4: Output Characteristics

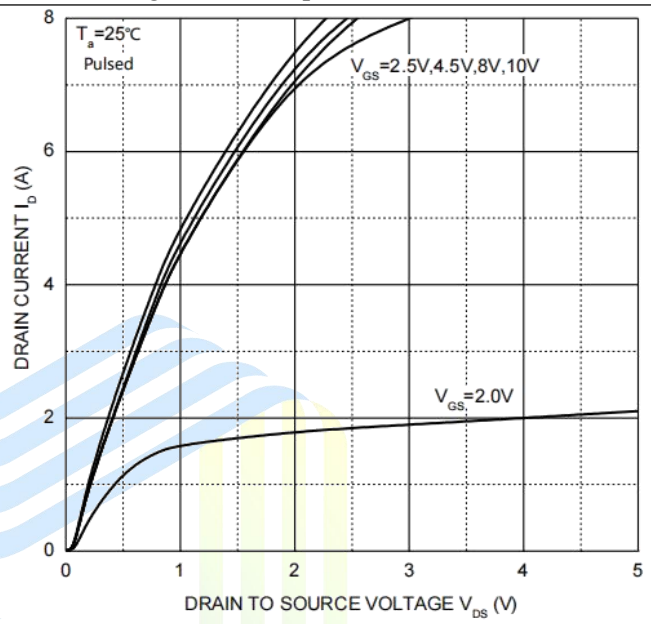


Figure 5: On-Resistance vs. Drain Current

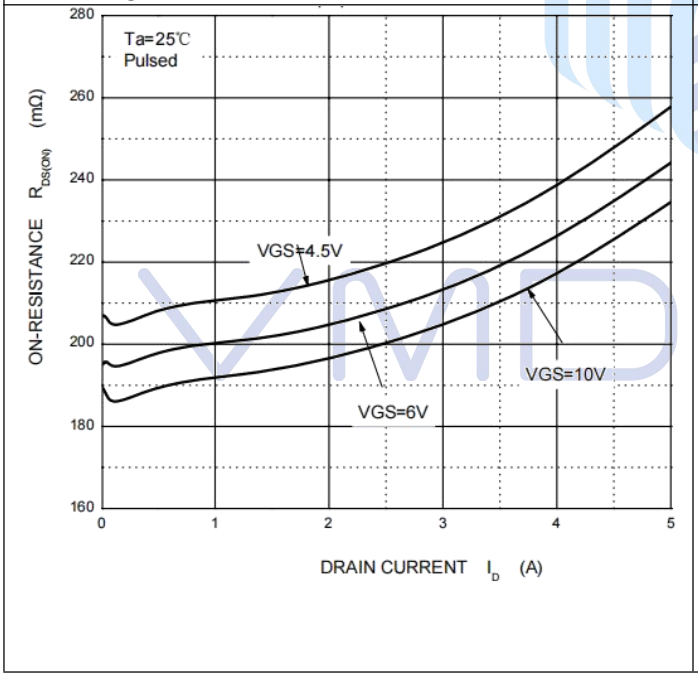


Figure 6: On-Resistance vs. Gate Voltage

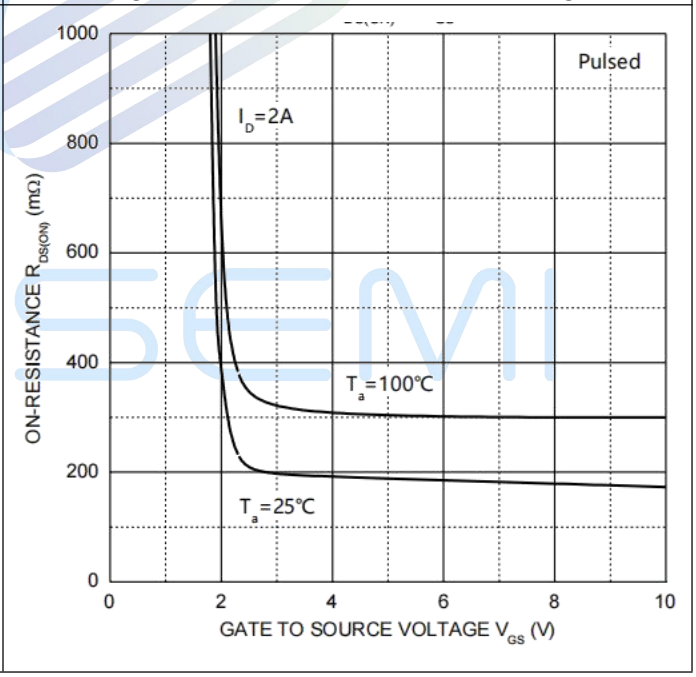


Figure 7: Body Diode Characteristics

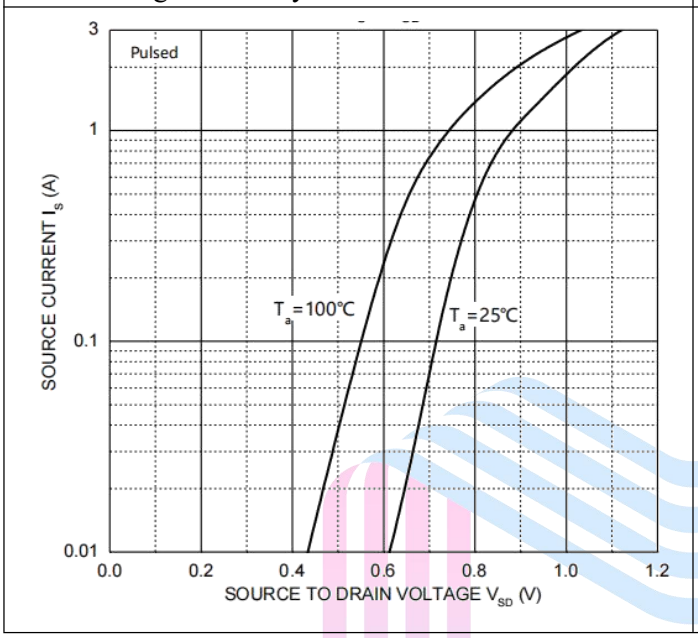
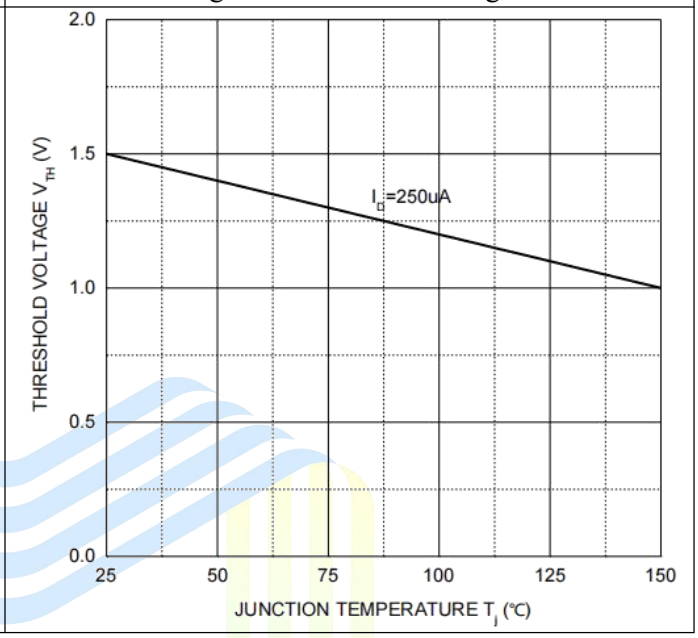
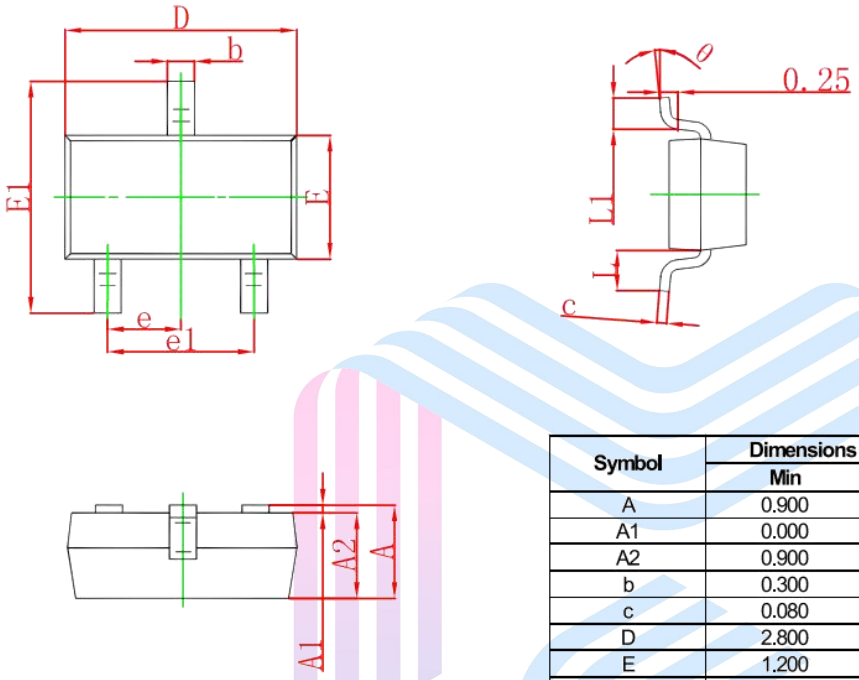


Figure 8: Threshold Voltage



Mechanical Dimensions:

SOT-23 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

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